58 and 60 are reproduced below without change in order that all of the claims being prosecuted may be easily viewed together.

44. (Fourfold Amended) A pair of adjacent stacked capacitors fabricated using a photolithographic process having a characteristic minimum photolithographic feature dimension on [relative to] a semiconductor substrate, the adjacent stacked capacitors respectively including a lower plate having a minimum lateral spacing from one another which is less than [a] the minimum photolithographic feature dimension [with which the capacitors are fabricated], each lower plate including a polysilicon plug having a diameter less than the minimum photolithographic feature dimension.

45. (Thrice Amended) [The capacitors of claim 44] A pair of adjacent stacked capacitors fabricated using a photolithographic process having a characteristic minimum photolithographic feature dimension on a semiconductor substrate, the adjacent stacked capacitors respectively including a lower plate having a minimum lateral spacing from one another which is less than the minimum photolithographic feature dimension wherein each of the pair of capacitors comprises:

a [stem] polysilicon plug having a diameter less than the minimum photolithographic feature dimension; and

in cross-section, at least two laterally opposed fins interconnected with and projecting laterally from the [stem] plug[, the stem having a minimum width which is less than the minimum photolithographic feature dimension].

51. The capacitors of claim 44, wherein the lower plates are formed from conductive polysilicon.

52. (Amended) The capacitors of claim 45, wherein the [stem] plug and fins are formed from conductive polysilicon.

53. The capacitors of claim 45, wherein the pair of stacked capacitors are coated with a capacitor dielectric layer.

54. (Amended) A pair of adjacent stacked capacitors fabricated using a photolithographic process having a characteristic minimum photolithographic feature dimension on [relative to] a semiconductor substrate, the adjacent stacked capacitors respectively including a lower plate having a minimum lateral spacing from one another which is less than [a] the minimum photolithographic feature dimension, each lower plate comprising a [stem] polysilicon plug having a diameter that is less than the minimum photolithographic feature dimension and, in cross-section, at least two laterally opposed fins interconnected with and projecting laterally from the plug [stem].

Cancel claim 55.

56. (Amended) The capacitors of claim 54 wherein the [stem] plug includes a minimum width which is less than the minimum photolithographic feature dimension.

Cancel claim 57.

58. The capacitors of claim 54, wherein the lower plates are formed from conductive polysilicon.

59. (Amended) The capacitors of claim 54, wherein the [stem] plug and fins are formed from conductive polysilicon.

60. The capacitors of claim 54, wherein the pair of stacked capacitors are coated with a capacitor dielectric layer.

Cancel claim 61.

62. (Amended) [The capacitors of claim 61] A pair of adjacent stacked capacitors fabricated using a photolithographic process having a characteristic minimum photolithographic feature dimension on a semiconductor substrate, the adjacent stacked capacitors respectively including a finned lower plate having a minimum lateral spacing from one another which is less than the minimum photolithographic feature dimension wherein each finned lower plate comprises:

a [stem] polysilicon plug; and

in cross-section, at least two laterally opposed fins interconnected with and projecting laterally from the [stem] plug, the [stem] plug having a minimum width which is less than the minimum photolithographic feature dimension.

Cancel claims 63-65.

66. (Amended) The capacitors of claim [61] 62, wherein the lower plates are formed from conductive polysilicon.

67. (Amended) The capacitors of claim 62, wherein the [stem] plug and fins are formed from conductive polysilicon.

68. (Amended) The capacitors of claim [61] 62, wherein the pair of stacked capacitors are coated with a capacitor dielectric layer.